

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2001-109150

(43)Date of publication of application : 20.04.2001

(51)Int.Cl.

G03F 7/039

C08L 83/06

G03F 7/075

G03F 7/095

G03F 7/26

(21)Application number : 11-284457

(71)Applicant : FUJI PHOTO FILM CO LTD

(22)Date of filing : 05.10.1999

(72)Inventor : UNO SEIJI

MIZUTANI KAZUYOSHI

(54) POSITIVE TYPE PHOTORESIST COMPOSITION

(57)Abstract:

PROBLEM TO BE SOLVED: To obtain a positive type photoresist composition excellent in shelf stability and giving a resist pattern free from development defects.

SOLUTION: The positive type photoresist composition contains an acid decomposable polysiloxane containing a structural unit having a naphthalene skeleton or an alkali-soluble polysiloxane containing a structural unit having a naphthalene skeleton, a photo-acid generator and a phenolic compound in which at least part of phenolic hydroxyl groups contained in its molecule is protected with an acid decomposable group or an aromatic or aliphatic carboxylic acid compound in which at least part of carboxyl groups contained in its molecule is protected with an acid decomposable group.

LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's
decision of rejection]

[Date of requesting appeal against examiner's
decision of rejection]

[Date of extinction of right]